

Hai Lu

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5224751/publications.pdf>

Version: 2024-02-01

144
papers

3,046
citations

172457

29
h-index

197818

49
g-index

147
all docs

147
docs citations

147
times ranked

3673
citing authors

#	ARTICLE	IF	CITATIONS
1	1.2 kV/25 A Normally off P-N Junction/AlGa _{0.3} N/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. IEEE Transactions on Power Electronics, 2022, 37, 26-30.	7.9	18
2	1.95-kV Beveled-Mesa NiO/Al _{0.2} Ga _{0.3} O _{0.3} Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. IEEE Transactions on Power Electronics, 2022, 37, 1223-1227.	7.9	60
3	Over 1200 V Normally-OFF p-NiO Gated AlGa _{0.3} N/GaN HEMTs on Si With a Small Threshold Voltage Shift. IEEE Electron Device Letters, 2022, 43, 268-271.	3.9	9
4	Near-infrared ITO-based photonic hypercrystals with large angle-insensitive bandgaps. Optics Letters, 2022, 47, 917.	3.3	11
5	70- μ m-Body Ga _{0.2} O _{0.3} Schottky Barrier Diode With 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. IEEE Electron Device Letters, 2022, 43, 773-776.	3.9	19
6	M-Plane Al _{0.2} Ga _{0.3} O _{0.3} Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. IEEE Electron Device Letters, 2022, 43, 541-544.	3.9	11
7	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. IEEE Transactions on Electron Devices, 2022, 69, 1918-1923.	3.0	1
8	4H-SiC n-i-p Extreme Ultraviolet Detector With Gradient Doping-Induced Surface Junction. IEEE Electron Device Letters, 2022, 43, 906-909.	3.9	2
9	High-Responsivity and Fast-Response Ultraviolet Phototransistors Based on Enhanced p-GaN/AlGa _{0.3} N/GaN HEMTs. ACS Photonics, 2022, 9, 2040-2045.	6.6	14
10	Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGa _{0.3} N Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. ACS Applied Materials & Interfaces, 2022, 14, 33525-33537.	8.0	4
11	Enhanced Contactless Salt-Collecting Solar Desalination. ACS Applied Materials & Interfaces, 2022, 14, 34151-34158.	8.0	13
12	ITO-based metamaterials for polarization-independent wide-angle mid-infrared thermal radiation. Case Studies in Thermal Engineering, 2022, 37, 102278.	5.7	2
13	Polarization-independent wide-angle flexible multiband thermal emitters enabled by layered quasi-periodic photonic crystal. Optics and Laser Technology, 2022, 156, 108474.	4.6	4
14	Sustainable Application of ZIF-8 for Heavy-Metal Removal in Aqueous Solutions. Sustainability, 2021, 13, 984.	3.2	36
15	Sustainable Solar Evaporation while Salt Accumulation. ACS Applied Materials & Interfaces, 2021, 13, 4935-4942.	8.0	46
16	Using a Modified Turian-Yuan Model to Enhance Heterogeneous Resistance in Municipal Sludge Transportation Pipeline. ACS Omega, 2021, 6, 7199-7211.	3.5	1
17	Quasiperiodic metamaterials empowered non-metallic broadband optical absorbers. Optics Express, 2021, 29, 13576.	3.4	6
18	Progress on AlGa _{0.3} N-based solar-blind ultraviolet photodetectors and focal plane arrays. Light: Science and Applications, 2021, 10, 94.	16.6	193

#	ARTICLE	IF	CITATIONS
19	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability. , 2021, , .		6
20	Nonreciprocal Tamm plasmon absorber based on lossy epsilon-near-zero materials. Optics Express, 2021, 29, 17736.	3.4	10
21	Interface roughness governed negative magnetoresistances in two-dimensional electron gases in AlGaIn/GaN heterostructures. Physical Review Materials, 2021, 5, .	2.4	2
22	A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. IEEE Photonics Journal, 2021, 13, 1-8.	2.0	5
23	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. IEEE Electron Device Letters, 2021, 42, 974-977.	3.9	29
24	46.4: Fabrication of InGaIn/GaN-based nano-LEDs for display applications. Digest of Technical Papers SID International Symposium, 2021, 52, 568-568.	0.3	0
25	The generating and modulating characteristics of bound states in the continuum for both TE and TM polarizations by one-dimensional photonic crystal slabs. Journal of Optics (United Kingdom), 2021, 23, 105202.	2.2	0
26	V_T Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. IEEE Electron Device Letters, 2021, 42, 1508-1511.	3.9	17
27	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. IEEE Transactions on Power Electronics, 2021, 36, 12163-12167.	7.9	19
28	An Ultraviolet Photon Counting Imaging System Based on a SiC SPAD Array. IEEE Photonics Technology Letters, 2021, 33, 1213-1216.	2.5	1
29	1.37 kV/12 A NiO ₂ -Ga ₂ O ₃ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. IEEE Transactions on Power Electronics, 2021, 36, 12213-12217.	7.9	77
30	Band evolution and Landau-Zener Bloch oscillations in strained photonic rhombic lattices. Optics Express, 2021, 29, 37503.	3.4	4
31	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. IEEE Electron Device Letters, 2021, 42, 1755-1758.	3.9	3
32	Higher-order exceptional point and Landau-Zener Bloch oscillations in driven non-Hermitian photonic Lieb lattices. APL Photonics, 2021, 6, .	5.7	17
33	Developing a Miniaturized Spectrophotometer Using 235 and 275 nm UVC-LEDs for Fast Detection of Nitrate in Natural Water and Wastewater Effluents. ACS ES&T Water, 2021, 1, 2548-2555.	4.6	4
34	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. IEEE Electron Device Letters, 2021, 42, 1743-1746.	3.9	4
35	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on InN Nitride Semiconductors. Advanced Materials, 2020, 32, e1904354.	21.0	34
36	Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900729.	1.8	4

#	ARTICLE	IF	CITATIONS
37	Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , 2020, 52, 1.	3.3	3
38	Plasmonic interference lithography by coupling the bulk plasmon polariton mode and the waveguide mode. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 135103.	2.8	8
39	High- k HfO ₂ -Based AlGaN/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 15-19.	2.1	19
40	Content and health risk assessment of heavy metals and polybrominated diphenyl ethers in fish from Songhua Lake (Jilin City), China. <i>Environmental Science and Pollution Research</i> , 2020, 27, 40848-40856.	5.3	6
41	Different I - V Behaviors and Leakage Current Mechanisms in AlGaN Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , 2020, 2, 2716-2720.	4.3	3
42	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2070028.	1.8	0
43	$\hat{\mu}$ -Ga ₂ O ₃ : A Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2020, , 1-1.	3.9	15
44	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 791-794.	2.5	10
45	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 706-709.	2.5	5
46	Observation of quincunx-shaped and dipole-like flatband states in photonic rhombic lattices without band-touching. <i>APL Photonics</i> , 2020, 5, 016107.	5.7	14
47	Do all screw dislocations cause leakage in GaN-based devices?. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	38
48	Azimuthal illumination enabled ultra-high polar angle sensitivity by a Bloch surface wave resonance refractive index sensor. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 215401.	2.8	1
49	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020, 41, 469-472.	3.9	16
50	Second-harmonic generation from 2D photonic crystal waveguide with simultaneous near-flat dispersions at fundamental frequency and second harmonic. <i>Optics Communications</i> , 2020, 472, 125885.	2.1	2
51	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	5
52	Br doped porous bismuth oxychloride micro-sheets with rich oxygen vacancies and dominating {001} facets for enhanced nitrogen photo-fixation performances. <i>Journal of Colloid and Interface Science</i> , 2019, 556, 111-119.	9.4	66
53	Precise Extraction of Dynamic R_{dson} Under High Frequency and High Voltage by a Double-Diode-Isolation Method. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 690-695.	2.1	10
54	Janus Ga ₂ SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , 2019, 3, 1900321.	5.8	13

#	ARTICLE	IF	CITATIONS
55	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. IEEE Electron Device Letters, 2019, 40, 1929-1932.	3.9	10
56	Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2019, 40, 379-382.	3.9	21
57	The Generalized Analytical Expression for the Resonance Frequencies of Plasmonic Nanoresonators Composed of Folded Rectangular Geometries. Scientific Reports, 2019, 9, 52.	3.3	4
58	Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. IEEE Photonics Journal, 2019, 11, 1-7.	2.0	10
59	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	3.3	24
60	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. ACS Applied Materials & Interfaces, 2019, 11, 20956-20964.	8.0	39
61	Investigation on the Activation Energy of Device Degradation and Switching Time in AlGaIn/GaN HEMTs for High-Frequency Application. IEEE Journal of the Electron Devices Society, 2019, 7, 417-424.	2.1	5
62	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. IEEE Photonics Technology Letters, 2019, 31, 447-450.	2.5	6
63	Observation and Modeling of Leakage Current in AlGaIn Ultraviolet Light Emitting Diodes. IEEE Photonics Technology Letters, 2019, 31, 1697-1700.	2.5	4
64	Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2019, 32, e2482.	1.9	4
65	Carbonized Bamboos as Excellent 3D Solar Vapor Generation Devices. Advanced Materials Technologies, 2019, 4, 1800593.	5.8	107
66	Low emissivity double sides antireflection coatings for silicon wafer at infrared region. Journal of Alloys and Compounds, 2018, 742, 729-735.	5.5	9
67	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. IEEE Photonics Technology Letters, 2018, 30, 805-808.	2.5	9
68	A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. IEEE Electron Device Letters, 2018, 39, 599-602.	3.9	43
69	Noise Characterization of Geiger-Mode 4H-SiC Avalanche Photodiodes for Ultraviolet Single-Photon Detection. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-5.	2.9	6
70	Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2018, 31, e2299.	1.9	1
71	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700368.	1.8	5
72	An ultra-sensitive and selective nitrogen dioxide sensor based on a novel P_{2C_2} monolayer from a theoretical perspective. Nanoscale, 2018, 10, 21936-21943.	5.6	28

#	ARTICLE	IF	CITATIONS
73	Enhanced Diffuse Reflectance and Microstructure Properties of Hybrid Titanium Dioxide Nanocomposite Coating. <i>Nanoscale Research Letters</i> , 2018, 13, 328.	5.7	14
74	Highly Efficient Spintronic Terahertz Emitter Enabled by Metal-Dielectric Photonic Crystal. <i>Advanced Optical Materials</i> , 2018, 6, 1800965.	7.3	59
75	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018, 18, 3414-3420.	9.1	33
76	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800069.	1.8	7
77	Guided Bloch surface wave resonance by near normal and near in-plane illuminations: the hyper azimuthal sensitivity. <i>Optics Express</i> , 2018, 26, 12769.	3.4	10
78	Improving the sensitivity of compound waveguide grating biosensor via modulated wavevector. <i>Applied Physics Express</i> , 2018, 11, 082202.	2.4	14
79	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018, 18, 1314.	3.8	13
80	Numerical study of the defect adamantine compound CuGaGeSe ₄ . <i>Molecular Physics</i> , 2018, 116, 1551-1557.	1.7	2
81	Photodetectors: Solvent-Based Soft Patterning of Graphene Lateral Heterostructures for Broadband High-Speed Metal-Semiconductor-Metal Photodetectors (Adv. Mater. Technol. 2/2017). <i>Advanced Materials Technologies</i> , 2017, 2, .	5.8	2
82	Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGaN Avalanche-Photodiodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	2.0	8
83	A self-powered high-performance graphene/silicon ultraviolet photodetector with ultra-shallow junction: breaking the limit of silicon?. <i>Npj 2D Materials and Applications</i> , 2017, 1, .	7.9	211
84	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , 2017, 9, 1-8.	2.0	8
85	Solvent-Based Soft Patterning of Graphene Lateral Heterostructures for Broadband High-Speed Metal-Semiconductor-Metal Photodetectors. <i>Advanced Materials Technologies</i> , 2017, 2, 1600241.	5.8	53
86	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase InGa ₂ O ₃ /ZnO Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 36997-37005.	8.0	158
87	Chiral Metamaterials: A Terahertz Controlled NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials (Advanced Optical Materials 18/2017). <i>Advanced Optical Materials</i> , 2017, 5, .	7.3	0
88	A Terahertz Controlled NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. <i>Advanced Optical Materials</i> , 2017, 5, 1700108.	7.3	15
89	An Improved Design for Solar-Blind AlGaIn Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	2.0	13
90	Abnormal mode splitting in photonic crystals micro-cavity containing highly dispersive metamaterials. <i>Journal of Optics (United Kingdom)</i> , 2017, 19, 125101.	2.2	0

#	ARTICLE	IF	CITATIONS
91	Tunneling-Hopping Transport Model for Reverse Leakage Current in InGaN/GaN Blue Light-Emitting Diodes. IEEE Photonics Technology Letters, 2017, 29, 1447-1450.	2.5	14
92	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH ₃ NH ₃ Pb(BrxI ^{1-\hat{a}'x)3 Crystals Synthesized via a Solvothermal Method. Scientific Reports, 2017, 7, 17695.}	3.3	18
93	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. IEEE Photonics Technology Letters, 2017, 29, 1603-1606.	2.5	10
94	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	13
95	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. IEEE Transactions on Electron Devices, 2017, 64, 4532-4539.	3.0	16
96	A method of applying compressive pre-stress to AlGaN barrier in AlGaN/GaN heterostructures by depositing an additional thermally mismatched dielectric. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2474-2478.	1.8	2
97	Improved Schottky contacts to InGaN alloys by a photoelectrochemical treatment. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1034-1038.	1.8	0
98	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 374-377.	0.8	7
99	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. Scientific Reports, 2016, 6, 23486.	3.3	21
100	High-Quality Crystal Growth and Characteristics of AlGaN-Based Solar-Blind Distributed Bragg Reflectors with a Tri-layer Period Structure. Scientific Reports, 2016, 6, 29571.	3.3	8
101	Polarization-independent split bull's eye antennas for infrared nano-photodetectors. Scientific Reports, 2016, 6, 39106.	3.3	2
102	Highly selective and sensitive phosphate anion sensors based on AlGaN/GaN high electron mobility transistors functionalized by ion imprinted polymer. Scientific Reports, 2016, 6, 27728.	3.3	43
103	Frequency response and design consideration of GaN SAM avalanche photodiodes. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	0
104	Guided Bloch surface wave resonance for biosensor designs. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2016, 33, 997.	1.5	20
105	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. IEEE Photonics Journal, 2016, 8, 1-7.	2.0	15
106	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. IEEE Photonics Technology Letters, 2016, 28, 2526-2528.	2.5	16
107	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. IEEE Photonics Technology Letters, 2016, 28, 1189-1192.	2.5	16
108	Developing LED UV fluorescence sensors for online monitoring DOM and predicting DBPs formation potential during water treatment. Water Research, 2016, 93, 1-9.	11.3	89

#	ARTICLE	IF	CITATIONS
109	Metamaterials: Anomalous Terahertz Reflection and Scattering by Flexible and Conformal Coding Metamaterials (Advanced Optical Materials 10/2015). Advanced Optical Materials, 2015, 3, 1373-1373.	7.3	11
110	Anomalous Terahertz Reflection and Scattering by Flexible and Conformal Coding Metamaterials. Advanced Optical Materials, 2015, 3, 1374-1380.	7.3	175
111	Determination of Temperature-Dependent Stress State in Thin AlGa _N Layer of AlGa _N /Ga _N HEMT Heterostructures by Near-Resonant Raman Scattering. Advances in Condensed Matter Physics, 2015, 2015, 1-6.	1.1	0
112	Metasurface-enhanced optical Tamm states and related lasing effect. Journal of the Optical Society of America B: Optical Physics, 2015, 32, 1624.	2.1	6
113	Surface Acceptor-Like Trap Model for Gate Leakage Current Degradation in Lattice-Matched InAlN/Ga _N HEMTs. IEEE Electron Device Letters, 2015, 36, 1281-1283.	3.9	7
114	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. IEEE Electron Device Letters, 2014, 35, 1034-1036.	3.9	30
115	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. IEEE Photonics Technology Letters, 2014, 26, 1136-1138.	2.5	53
116	High-Gain AlGa _N Solar-Blind Avalanche Photodiodes. IEEE Electron Device Letters, 2014, 35, 372-374.	3.9	97
117	Reverse leakage current in AlGa _N -based ultraviolet light-emitting diodes. Science Bulletin, 2014, 59, 1276-1279.	1.7	6
118	Sex- and season-dependent differences in telomere length and telomerase activity in the leaves of ash and willow. SpringerPlus, 2014, 3, 163.	1.2	4
119	Significant Performance Improvement in AlGa _N Solar-Blind Avalanche Photodiodes by Exploiting the Built-In Polarization Electric Field. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 187-192.	2.9	30
120	Plasmonic Fraunhofer-wavelength narrow-band filter based on calcium film. Optik, 2014, 125, 3355-3357.	2.9	0
121	Energy Consumption Analysis of Sludge Transport Pipeline System Based on GA-DE Hybrid Algorithm. Journal of Chemical Engineering of Japan, 2014, 47, 621-627.	0.6	3
122	Solar-blind ultraviolet AlInN/AlGa _N distributed Bragg reflectors. Applied Physics Letters, 2013, 102, .	3.3	17
123	A flexible wideband bandpass terahertz filter using multi-layer metamaterials. Applied Physics B: Lasers and Optics, 2013, 113, 285-290.	2.2	36
124	The Fano-type transmission and field enhancement in heterostructures composed of epsilon-near-zero materials and truncated photonic crystals. Applied Physics Letters, 2013, 103, 201902.	3.3	7
125	Exploitation of Polarization in Back-Illuminated AlGa _N Avalanche Photodiodes. IEEE Photonics Technology Letters, 2013, 25, 1510-1513.	2.5	25
126	High Quantum Efficiency Ga _N -Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. IEEE Photonics Technology Letters, 2013, 25, 652-654.	2.5	45

#	ARTICLE	IF	CITATIONS
127	High-efficiency nonlinear platform with usage of metallic nonlinear susceptibility. Optics Letters, 2013, 38, 1283.	3.3	4
128	Light tunneling effect tuned by a meta-interface with electromagnetically-induced-transparency-like properties. Applied Physics Letters, 2013, 102, .	3.3	7
129	Optical Tamm states in hetero-structures with highly dispersive planar plasmonic metamaterials. Applied Physics Letters, 2013, 102, .	3.3	17
130	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. Applied Physics Letters, 2012, 100, 243505.	3.3	82
131	Characteristics of polarization-doped N-face III-nitride light-emitting diodes. Applied Physics Letters, 2012, 100, 073507.	3.3	20
132	Improvements in Microstructure and Leakage Current of High-In-Content InGaN p-i-n Structure by Annealing. IEEE Photonics Technology Letters, 2012, 24, 1478-1480.	2.5	3
133	Ultra-Low Dark Current AlGaIn-Based Solar-Blind Metal-Semiconductor-Metal Photodetectors for High-Temperature Applications. IEEE Sensors Journal, 2012, 12, 2086-2090.	4.7	75
134	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. IEEE Photonics Technology Letters, 2012, 24, 2203-2205.	2.5	7
135	Enhanced nonlinear optical response of a planar thick metal film combined with a truncated photonic crystal. Optics Communications, 2012, 285, 5416-5419.	2.1	6
136	GaN MSM photodetectors fabricated on bulk GaN with low dark-current and high UV/visible rejection ratio. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2473-2475.	0.8	12
137	Field-dependent carrier trapping induced kink effect in AlGaIn/GaN high electron mobility transistors. Applied Physics Letters, 2011, 98, .	3.3	40
138	Fabrication of blue and green non-polar InGaIn/GaN multiple quantum well light-emitting diodes on LiAlO ₂ (100) substrates. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1404-1406.	1.8	4
139	InGaIn/GaN multi-quantum-well-based light-emitting and photodetective dual-functional devices. Frontiers of Optoelectronics in China, 2009, 2, 442-445.	0.2	1
140	Structural and optical characteristics of Al _x Ga _{1-x} N/AlN superlattice. Science in China Series D: Earth Sciences, 2009, 52, 332-335.	0.9	1
141	Modification of the valence band structures of polar and nonpolar plane wurtzite-GaN by anisotropic strain. Journal of Applied Physics, 2009, 106, 023714.	2.5	23
142	Strain- and Compositional Modulation of the Near-Band-Edge Band Structures of AlN and Its Ternary Alloys with GaN and InN. , 2009, , .		0
143	An experimental study on the pretreatment of lignite upgrading wastewater using the Fenton oxidation method. Chemical Papers, 0, , 1.	2.2	0
144	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. , 0, .		1